[Claims]

[Claim 1]

Method for batch etching of tungsten film and titanium nitride film using an etchant composition comprising a nitric acid, water, a phosphoric acid and between 10.1 and 40.0 wt% of at least one selected from the group consisting of a sulfuric acid and an aliphatic sulfonic acid.

[Claim 2]

The method of claim 1, wherein the at least one selected from a sulfuric acid and an aliphatic sulfonic acid is in an amount between 11.73 and 40.0 wt %.

[Claim 3]

The method according to Claim 1 or 2, wherein the aliphatic sulfonic acid is a methanesulfonic acid.

[Claim 4]

The method according to any one of Claim 1 to 3, wherein the temperature of the etching composition at which the etching is performed is 50 °C or higher.

[Claim 5]

The method according to any one of Claims 1 to 4 for generating a pattern having a three-dimensional structure.